

SuperMOS – PDFN3*3-8L -30V BV_{DSS}, 8mΩ R_{DS(on)}, P-channel MOSFET

1. Description

The ESN7409 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESN7409 is Pb-free.

2. Features

- -30V, R_{DS(ON)}=8.0mΩ(TYP.) @V_{GS}=-10V
- R_{DS(ON)}=11.5mΩ(TYP.) @V_{GS}=-4.5V
- Fast Switching
- High density cell design for low R_{DS(on)}
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED!

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel size
ESN7409	PDFN3*3-8L	ESN7409/LOT	Halogen free	Tape & Reel	5,000 PCS	UL 94V-0	13 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate		
1/2/3	Source		
5/6/7/8	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	-30	V
Gate-Source Voltage		V_{GS}	± 25	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	-39	A
	$T_C=75^\circ\text{C}$		-30	
Maximum Power Dissipation	$T_C=25^\circ\text{C}$	P_D	30	W
	$T_C=75^\circ\text{C}$		17.8	
Pulsed Drain Current ^a		I_{DM}	-156	A
Operating Junction Temperature		T_J	150	°C
Storage Temperature Range		T_{stg}	-55 to +150	°C

Thermal resistance ratings

Parameter		Symbol	Typical	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10 \text{ s}$	$R_{\theta JA}$	40	°C/W
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	4.2	

Note:

a: Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			-1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 25V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.4	-2.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-12A$		8	13	m Ω
		$V_{GS}=-4.5V, I_D=-7A$		11.5	18	
Forward Trans conductance	g_{FS}	$V_{DS}=-5.0V, I_D=-6A$			100	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz,$ $V_{DS}=-15V$		1780		pF
Output Capacitance	C_{OSS}			235		
Reverse Transfer Capacitance	C_{RSS}			200		
Gate Resistance	R_g	$f=1MHz$		2.5		Ω
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=-10V, V_{DS}=-15V,$ $I_D=-20A$		46		nC
Gate-to-Source Charge	Q_{GS}			1.0		
Gate-to-Drain Charge	Q_{GD}			1.4		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=-10V, V_{DS}=-15V,$ $R_L=1\Omega, R_G=3\Omega$		8		ns
Rise Time	t_r			27		
Turn-Off Delay Time	$t_{d(OFF)}$			68		
Fall Time	t_f			39		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-1.0A$		-0.75	-1.5	V

7. Typical Characteristic

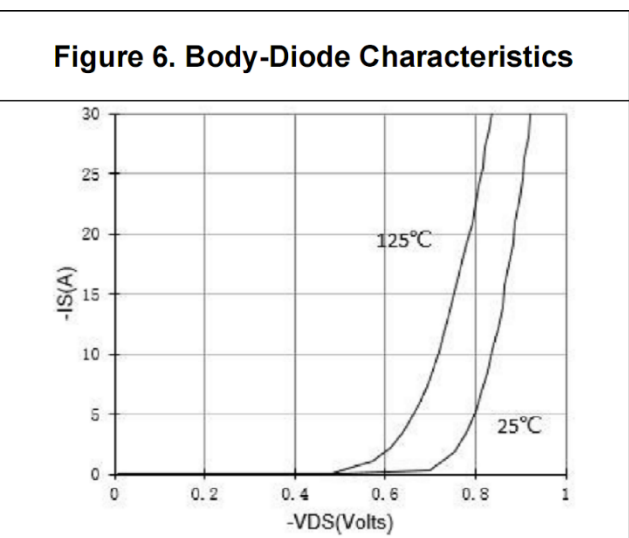
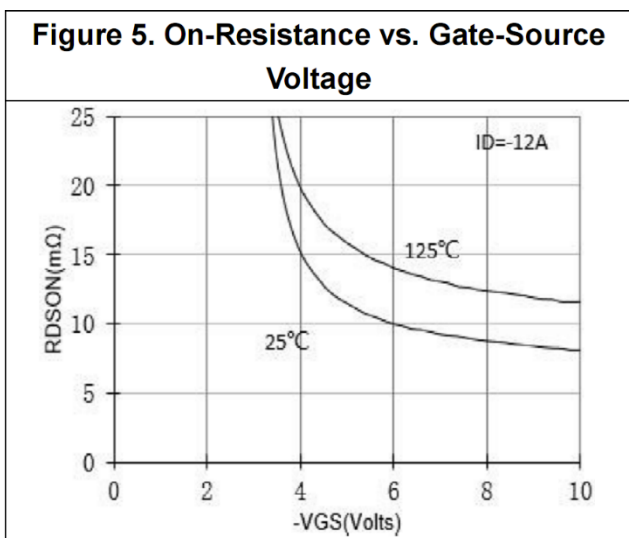
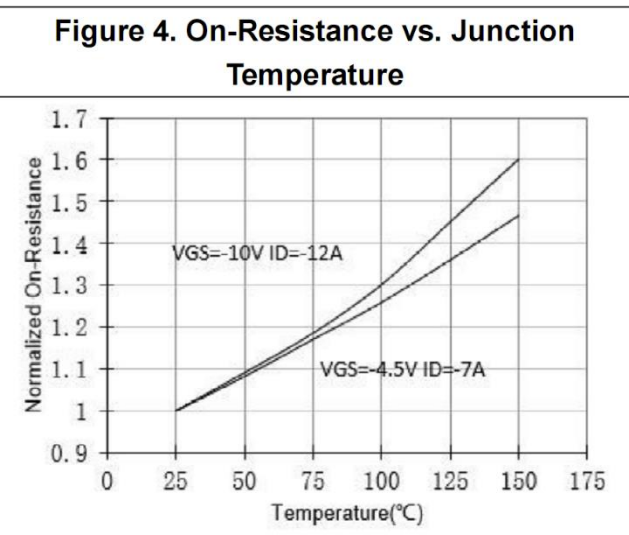
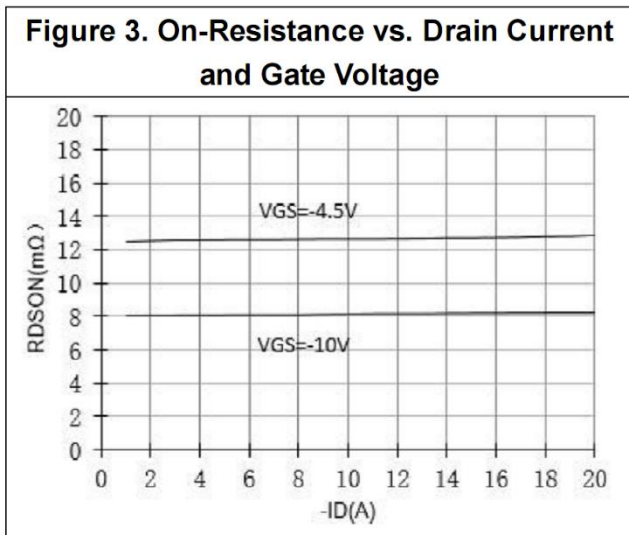
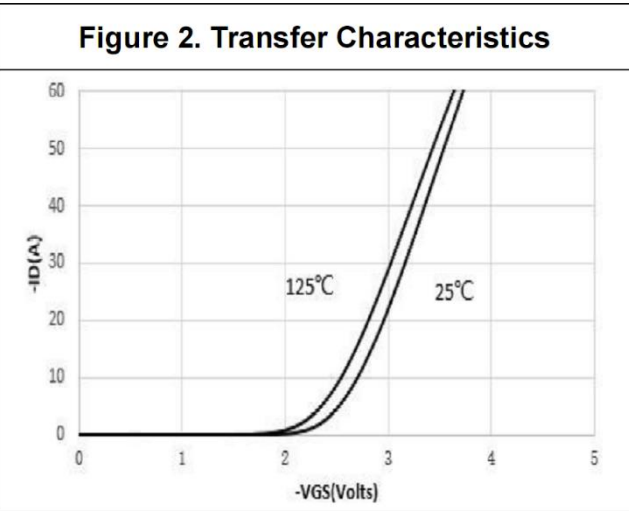
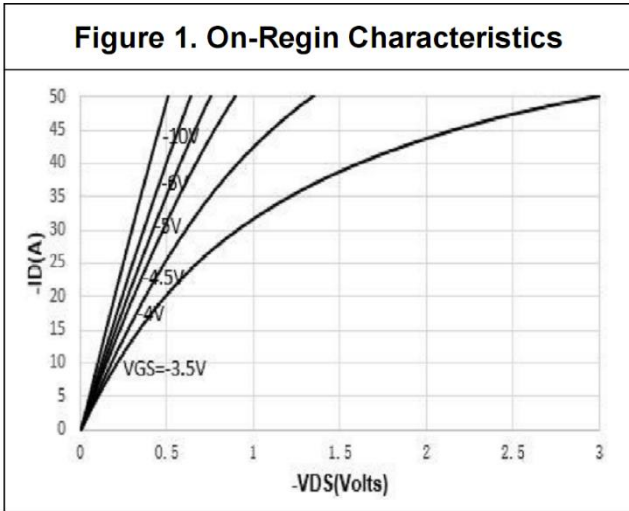


Figure 7. Gate-Charge Characteristics

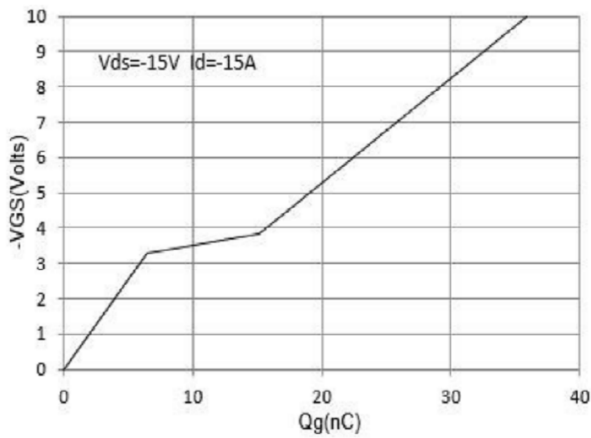


Figure 8. Capacitance Characteristics

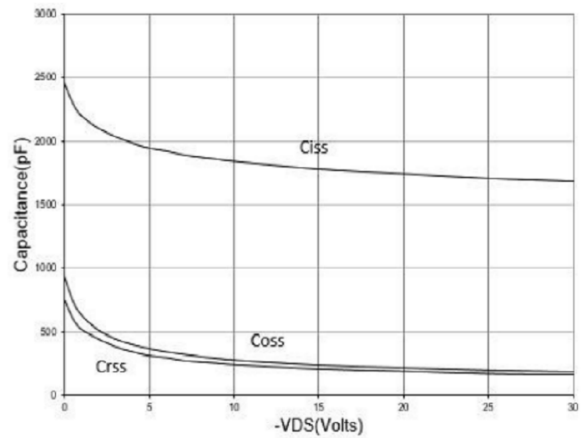


Figure 9. Maximum Forward Biased Safe Operating Area

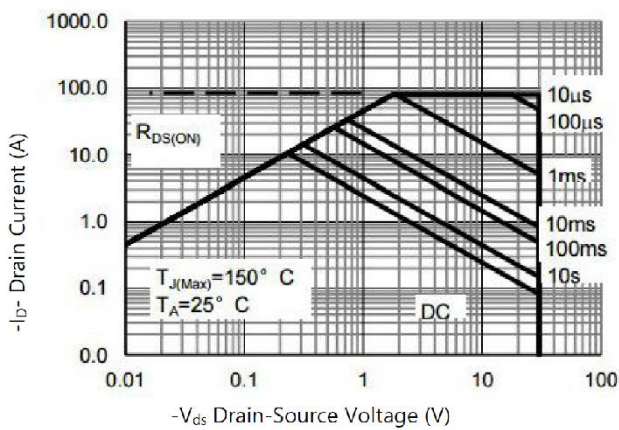
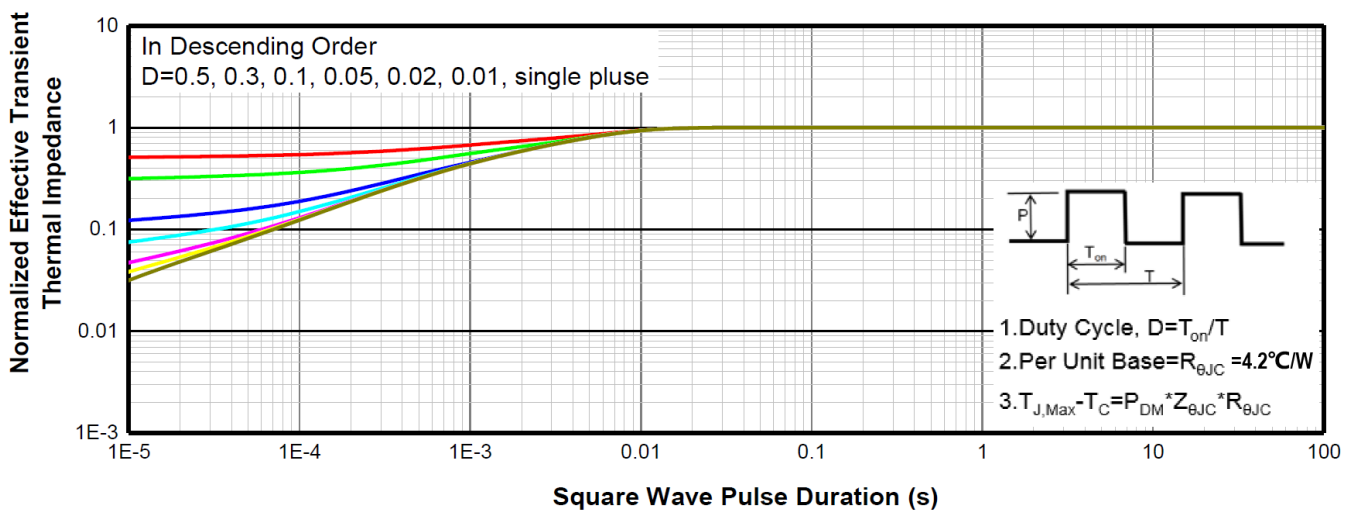
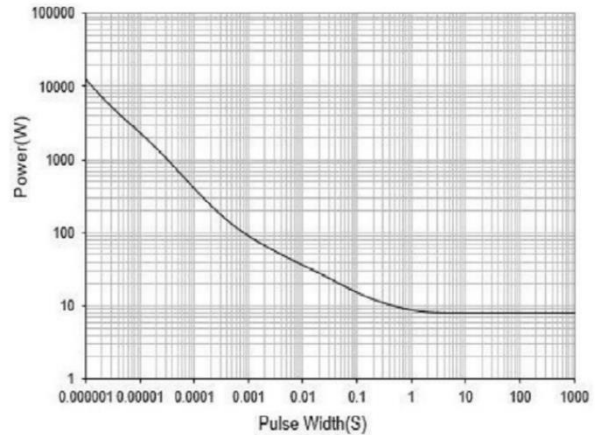
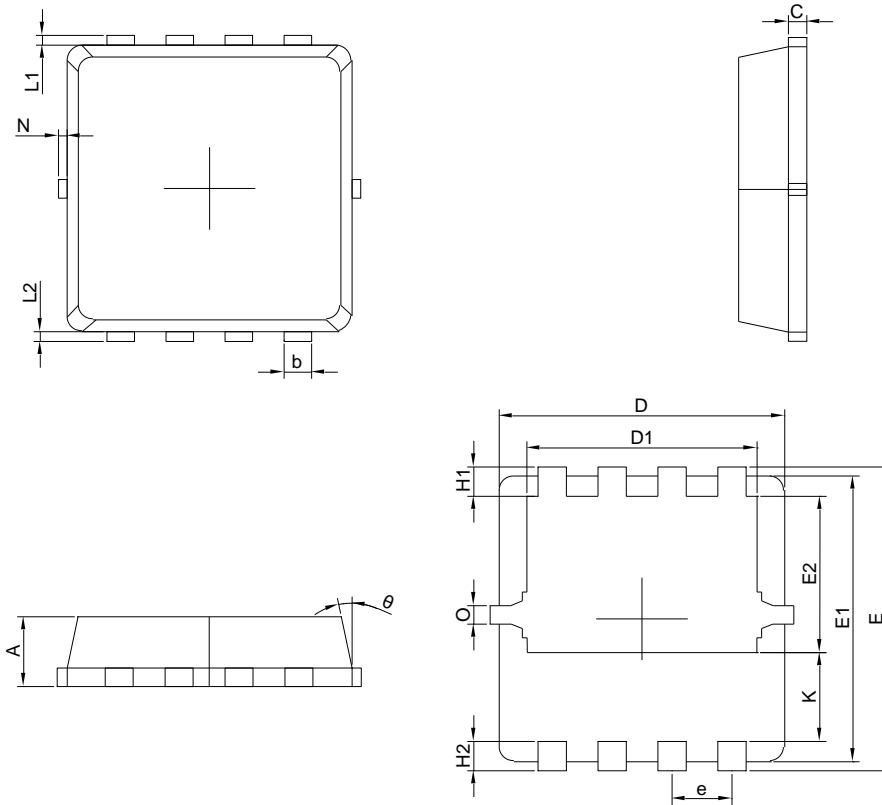


Figure 10. Single Pulse Power Rating Junction-to-Ambient



Transient Thermal Response (Junction-to-Case)

8. Dimension (PDFN3*3-8L)



Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.65	0.75	0.85	e	0.65 BSC.		
b	0.25	0.30	0.35	H1	0.21	0.31	0.41
C	0.15	0.20	0.25	H2	0.30	0.40	0.50
D	3.00	3.10	3.20	K	0.78	0.88	0.98
D1	2.40	2.50	2.60	L1/L2	0.10 REF.		
E	3.20	3.30	3.40	theta	11°	12°	13°
E1	3.00	3.10	3.20	N	0	-	0.15
E2	1.60	1.70	1.80	O	0.2 REF.		

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